



## **ZVP0120ASTOB Information**



For Reference Only

Part Number ZVP0120ASTOB
Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 200V 0.11A TO92-3

Package E-Line-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **ZVP0120ASTOB Specifications**

Manufacturer Part NumberZVP0120ASTOBManufacturerDiodes IncorporatedCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageE-Line-3Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C110mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ ImAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds100pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs32 Ohm @ 125mA, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageE-Line (TO-92 compatible)Package / CaseE-Line-3Report errors?		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  E-Line-3  Series  - FET Type  P-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  110mA (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ### 20V  ### 32 OMm (Ta)  ### 33 OMm (Ta)  ### 34 OMm (Ta)  ### 35 OMm (Ta)  ### 36 OMm (Ta)  ### 37 OMM (Ta)  ### 37 OMM (Ta)  ### 36 OMM (Ta)  ### 37 OMM (Ta)  ### 38 OMM (Ta)  ### 39 OMM (Ta)  ### 30 OMM (Ta)  ### 30 OMM (Ta)  ### 30 OMM (Ta)  ### 31 OMM (Ta)  ### 31 OMM (Ta)  ### 32 OMM (Ta)  ### 32 OMM (Ta)  ### 33 OMM (Ta)  ### 34 OMM (Ta)  ### 35 OMM (Ta)  ### 36 OMM (Ta)  ### 36 OMM (Ta)  ### 36 OMM (Ta)  ### 37 OMM (Ta)  ### 38 OMM	Manufacturer Part Number	ZVP0120ASTOB
Package         E-Line-3           Series         -           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         200V           Current - Continuous Drain (Id) @ 25°C         110mA (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ 1mA           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         100pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         700mW (Ta)           Rds On (Max) @ Id, Vgs         32 Ohm @ 125mA, 10V           Operating Temperature         -           Mounting Type         Through Hole           Supplier Device Package         E-Line (TO-92 compatible)           Package / Case         E-Line-3	Manufacturer	Diodes Incorporated
PackageE-Line-3Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C110mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds100pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs32 Ohm @ 125mA, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageE-Line (TO-92 compatible)Package / CaseE-Line-3	Category	Discrete Semiconductor Products
Series - Carbon Series - P-Channel P-Channel MOSFET (Metal Oxide) Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 110mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 100pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 700mW (Ta) Rds On (Max) @ Id, Vgs 32 Ohm @ 125mA, 10V Operating Temperature - Mounting Type Through Hole Supplier Device Package E-Line (TO-92 compatible) Package / Case		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C110mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds100pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs32 Ohm @ 125mA, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageE-Line (TO-92 compatible)Package / CaseE-Line-3	Package	E-Line-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 110mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 100pF @ 25V Vgs (Max)  **EUV** FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 32 Ohm @ 125mA, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package E-Line (TO-92 compatible) Package / Case  **Case**  **InouA (Ta) 10V **Capacitance (Ciss) (Max) @ Vds 100pF @ 25V **EUV** **InouA (Ta) 3.5V @ 1mA 3.5V @ 1	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  110mA (Ta)  10V  Vgs(th) (Max) @ Id  3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Supplier Device Package  Package / Case  200V  110mA (Ta)  10V  10V  10V  10V  10V  10V  10V  10	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 110mA (Ta)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs -  Input Capacitance (Ciss) (Max) @ Vds 100pF @ 25V  Vgs (Max) ±20V  FET Feature -  Power Dissipation (Max) 700mW (Ta)  Rds On (Max) @ Id, Vgs 32 Ohm @ 125mA, 10V  Operating Temperature -  Mounting Type Through Hole  Supplier Device Package E-Line (TO-92 compatible)  Package / Case E-Line-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  3.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  32 Ohm @ 125mA, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  FUND Signature  100pF @ 25V  25V  20V  20W  100pF @ 25V  20V  20V  20V  20V  20V  20V  20V	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  Supplier Device Package  E-Line-3	Current - Continuous Drain (Id) @ 25°C	110mA (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  32 Ohm @ 125mA, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  E-Line (TO-92 compatible)  Package / Case  -  E-Line-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  32 Ohm @ 125mA, 10V  Operating Temperature  - Mounting Type  Through Hole  Supplier Device Package  E-Line (TO-92 compatible)  Package / Case  E-Line-3	Vgs(th) (Max) @ Id	3.5V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)700mW (Ta)Rds On (Max) @ Id, Vgs32 Ohm @ 125mA, 10VOperating Temperature-Mounting TypeThrough HoleSupplier Device PackageE-Line (TO-92 compatible)Package / CaseE-Line-3	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - ToomW (Ta)  Power Dissipation (Max) 700mW (Ta)  Rds On (Max) @ Id, Vgs 32 Ohm @ 125mA, 10V  Operating Temperature - Through Hole  Supplier Device Package E-Line (TO-92 compatible)  Package / Case E-Line-3	Input Capacitance (Ciss) (Max) @ Vds	100pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  Towns A (TO-92 compatible)  E-Line-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 32 Ohm @ 125mA, 10V  Operating Temperature -  Mounting Type Through Hole  Supplier Device Package E-Line (TO-92 compatible)  Package / Case E-Line-3	FET Feature	-
Operating Temperature -  Mounting Type Through Hole  Supplier Device Package E-Line (TO-92 compatible)  Package / Case E-Line-3	Power Dissipation (Max)	700mW (Ta)
Mounting Type Through Hole Supplier Device Package E-Line (TO-92 compatible) Package / Case E-Line-3	Rds On (Max) @ Id, Vgs	32 Ohm @ 125mA, 10V
Supplier Device Package E-Line (TO-92 compatible) Package / Case E-Line-3	Operating Temperature	-
Package / Case E-Line-3	Mounting Type	Through Hole
-	Supplier Device Package	E-Line (TO-92 compatible)
Report errors?	Package / Case	E-Line-3
		Report errors?

### **ZVP0120ASTOB Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **ZVP0120ASTOB Payment Methods**



















### **ZVP0120ASTOB Shipping Methods**













If you have any question about ZVP0120ASTOB, please do not hesitate to contact us!

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